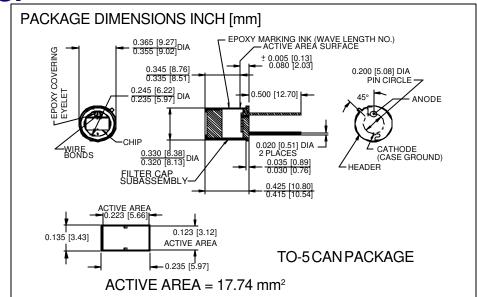
PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic DETECTORS INC. (center wavelength 950 nm) Type PDI-V495





RESPONSIVITY (A/W)

FEATURES

- High transmission
- 10⁻⁴ rejection
- +/- 2nm CWL
- Match to 940 nm LED

DESCRIPTION

The PDI-V495 is a silicon, PIN planar diffused, photodiode with a wide band interferance filter. The detector filter combination has a wide 65 nm half bandwidth designed for low noise photovoltaic applications. Packaged in a TO-5 metal can.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

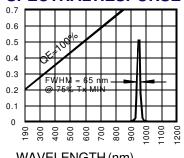
SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature	-20	+85	°C	
To	Operating Temperature Range	-15	+70	°C	
Ts	Soldering Temperature*		+240	°C	
IL	Light Current		0.5	mA	

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- I.R. sensor
- GaAs LED sensor
- Spectrophotometry
- Chemistry instrumentation

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μΑ
ΙD	Dark Current	H = 0, V _R = 10 mV		10	50	pА
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
Сл	Junction Capacitance	H = 0, V _R = 10 V**		1700		рF
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		950		nm
HBW	Half Bandwidth	(FWHM)		65		nm
VBR	Breakdown Voltage	I = 10 µuA	50	75		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ √Hz
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS